Form PTO 1449	Atty. Docket Number	Serial Number
U.S. Department of Commerce Patent and Trademark Office	NITT.0155	10/660,657
	Applicant Hanzawa et al	
Information Disclosure Statement by Applicant	Filing Date 09/12/03	Group AU 2824

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Examiner Initial	Cited in parent	Document Number	Date	Name	Class	Subc lass	Filing Date
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Examiner	Date Considered
[signature]	02/19/2004

Examiner: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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